



SANYO Semiconductors

DATA SHEET

5HN01S — N-Channel Silicon MOSFET

General-Purpose Switching Device Applications

Features

- Low ON-resistance.
- Ultrahigh-speed switching.
- 4V drive.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		50	V
Gate-to-Source Voltage	V _{GSS}		±20	V
Drain Current (DC)	I _D		0.1	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	0.4	A
Allowable Power Dissipation	P _D		0.15	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	I _D =1mA, V _{GS} =0V	50			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _D =50V, V _{GS} =0V			1	μA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±16V, V _D =0V			±10	μA
Cutoff Voltage	V _{GS(off)}	V _D =10V, I _D =100μA	1		2.4	V
Forward Transfer Admittance	y _{fs}	V _D =10V, I _D =50mA	85	120		mS
Static Drain-to-Source On-State Resistance	R _{DS(on)1}	I _D =50mA, V _{GS} =10V		5.8	7.5	Ω
	R _{DS(on)2}	I _D =30mA, V _{GS} =4V		7.5	10.5	Ω
Input Capacitance	C _{iss}	V _D =10V, f=1MHz		6.2		pF
Output Capacitance	C _{oss}	V _D =10V, f=1MHz		4.4		pF
Reverse Transfer Capacitance	C _{rss}	V _D =10V, f=1MHz		1.5		pF
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		10		ns
Rise Time	t _r	See specified Test Circuit.		11		ns
Turn-OFF Delay Time	t _{d(off)}	See specified Test Circuit.		105		ns
Fall Time	t _f	See specified Test Circuit.		75		ns

Marking : YC

Continued on next page.

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5HN01S

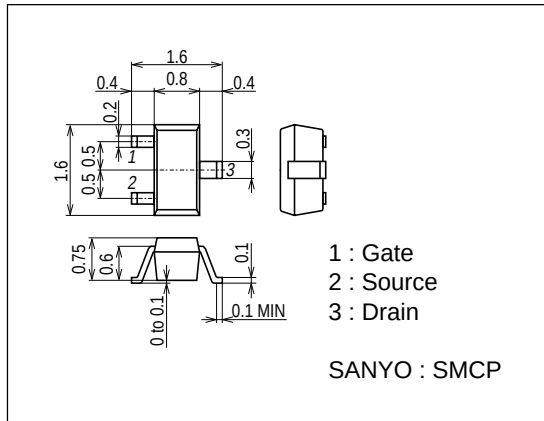
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Total Gate Charge	Qg	V _{DS} =10V, V _{GS} =10V, I _D =100mA		1.40		nC
Gate-to-Source Charge	Qgs	V _{DS} =10V, V _{GS} =10V, I _D =100mA		0.21		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =10V, V _{GS} =10V, I _D =100mA		0.34		nC
Diode Forward Voltage	V _{SD}	I _S =100mA, V _{GS} =0V		0.85	1.2	V

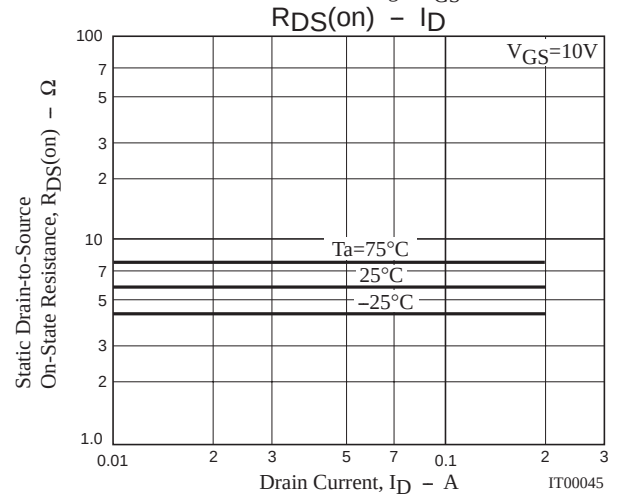
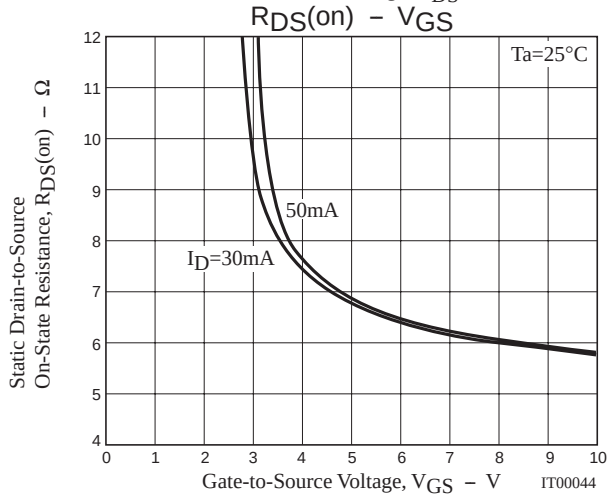
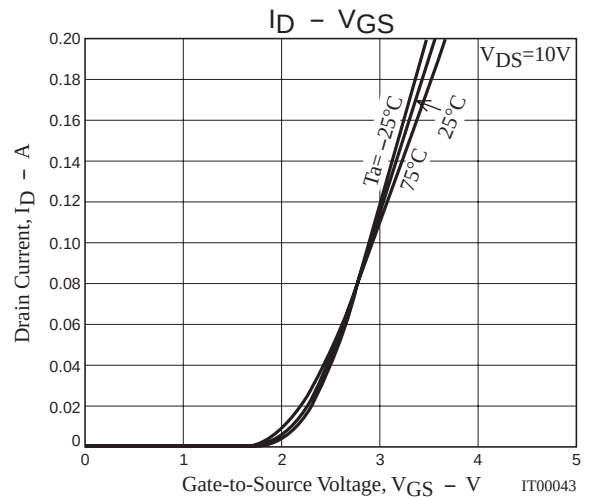
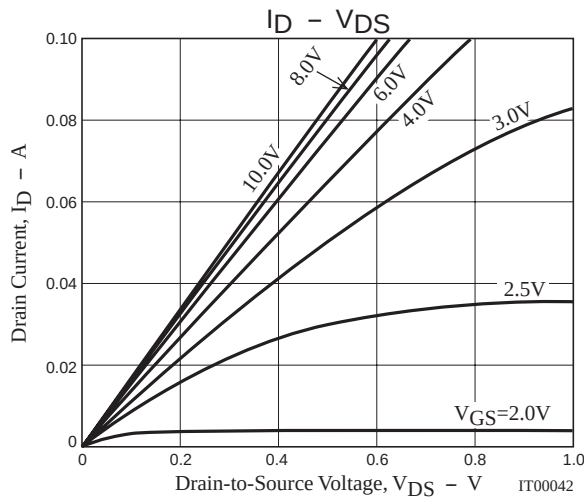
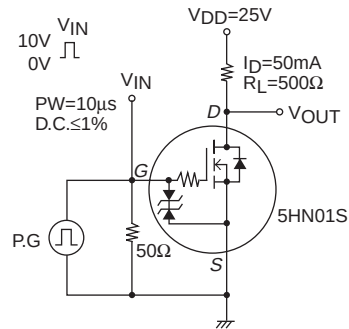
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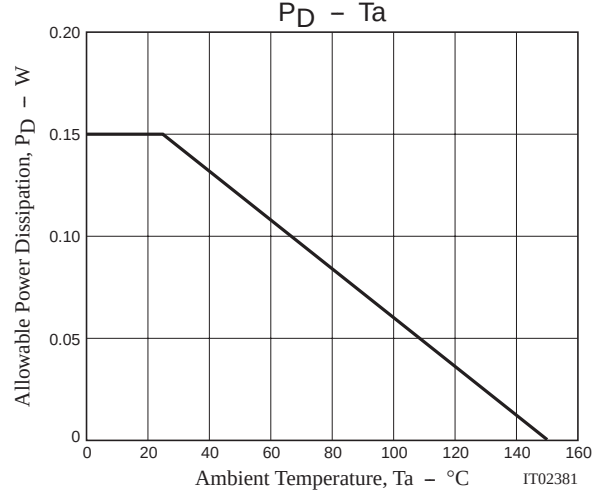
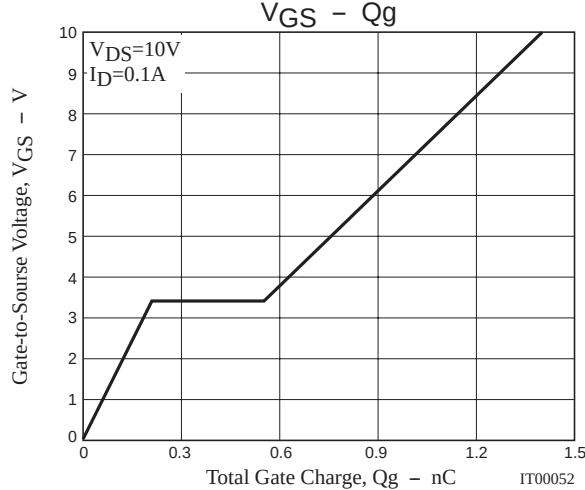
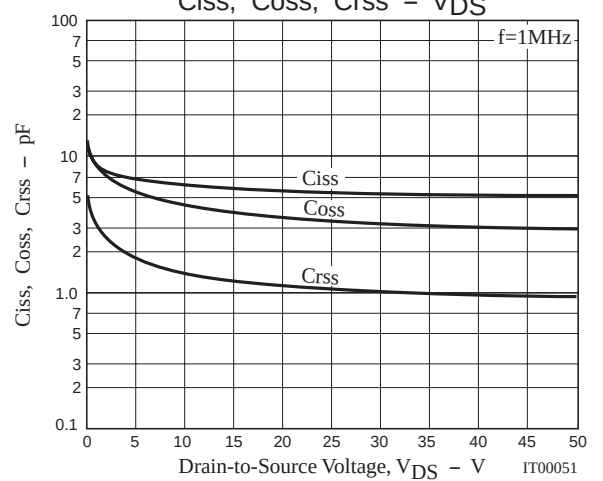
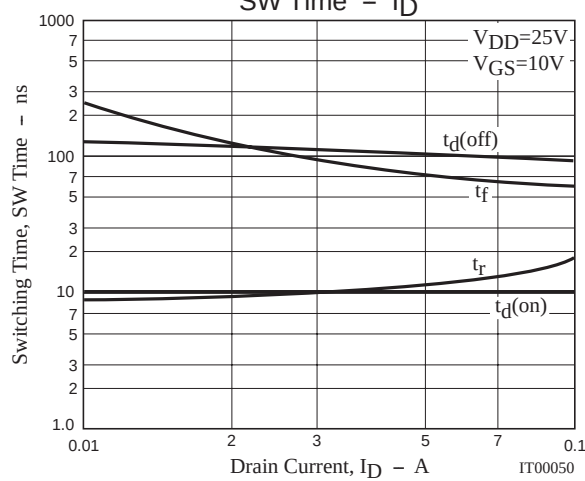
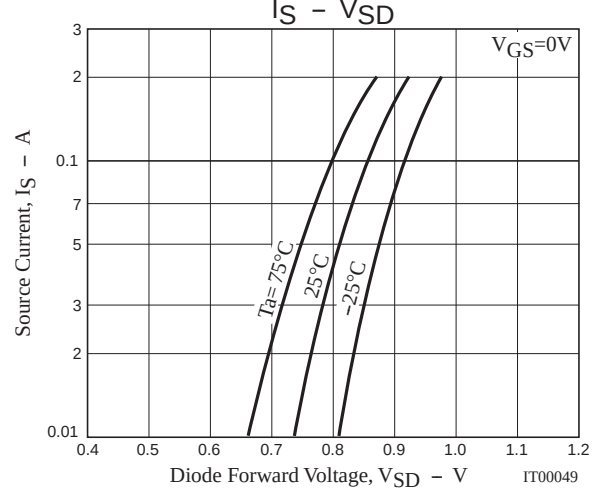
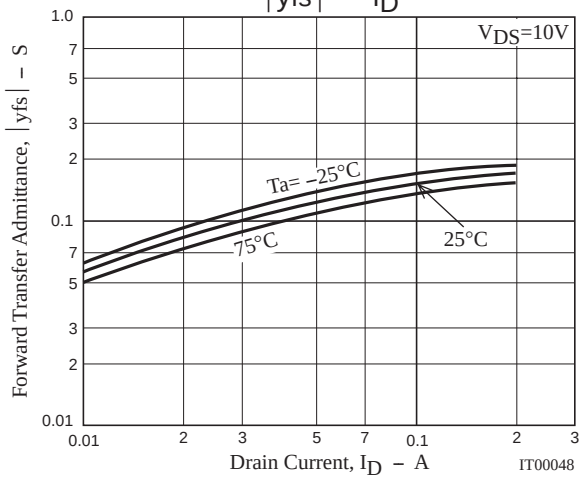
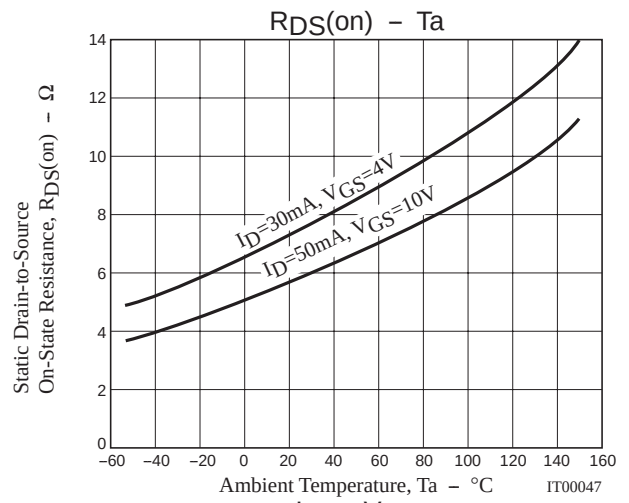
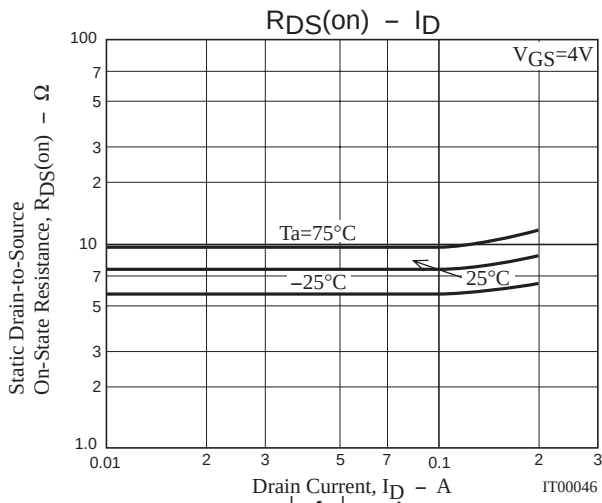
unit : mm

7027-004



Switching Time Test Circuit





Note on usage : Since the 5HN01S is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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